

Silicon NPN Power Transistors

2SC3710

DESCRIPTION

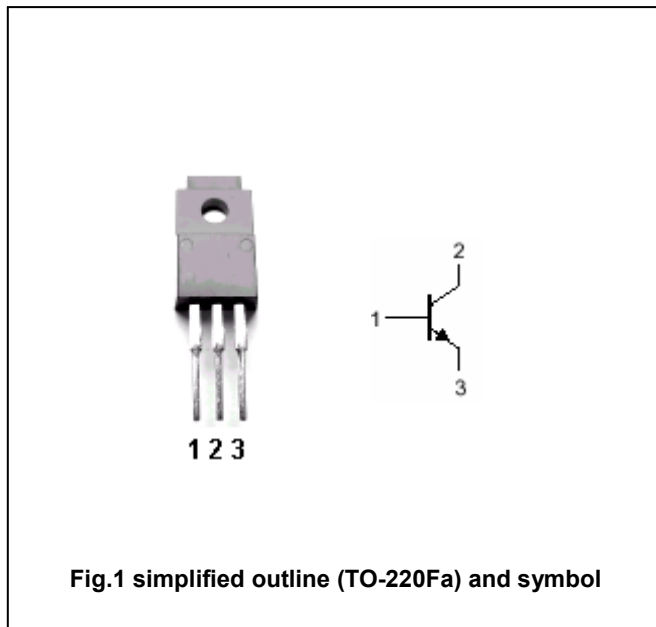
- With TO-220Fa package
- Complement to type 2SA1452
- Low collector saturation voltage
- High speed switching time

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	80	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		12	A
I _B	Base current		2	A
P _C	Collector dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =0.3A		0.2	0.4	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =0.3A		0.9	1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =80V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =1V	70		240	
h _{FE-2}	DC current gain	I _C =6A ; V _{CE} =1V	40			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V, f=1MHz		220		pF
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		80		MHz

Switching times

t _{on}	Turn-on time	I _{B1} =-I _{B2} =0.3A V _{CC} ≈30V , R _L =5Ω		0.2		μs
t _s	Storage time			1.0		μs
t _f	Fall time			0.2		μs

◆ h_{FE-1} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

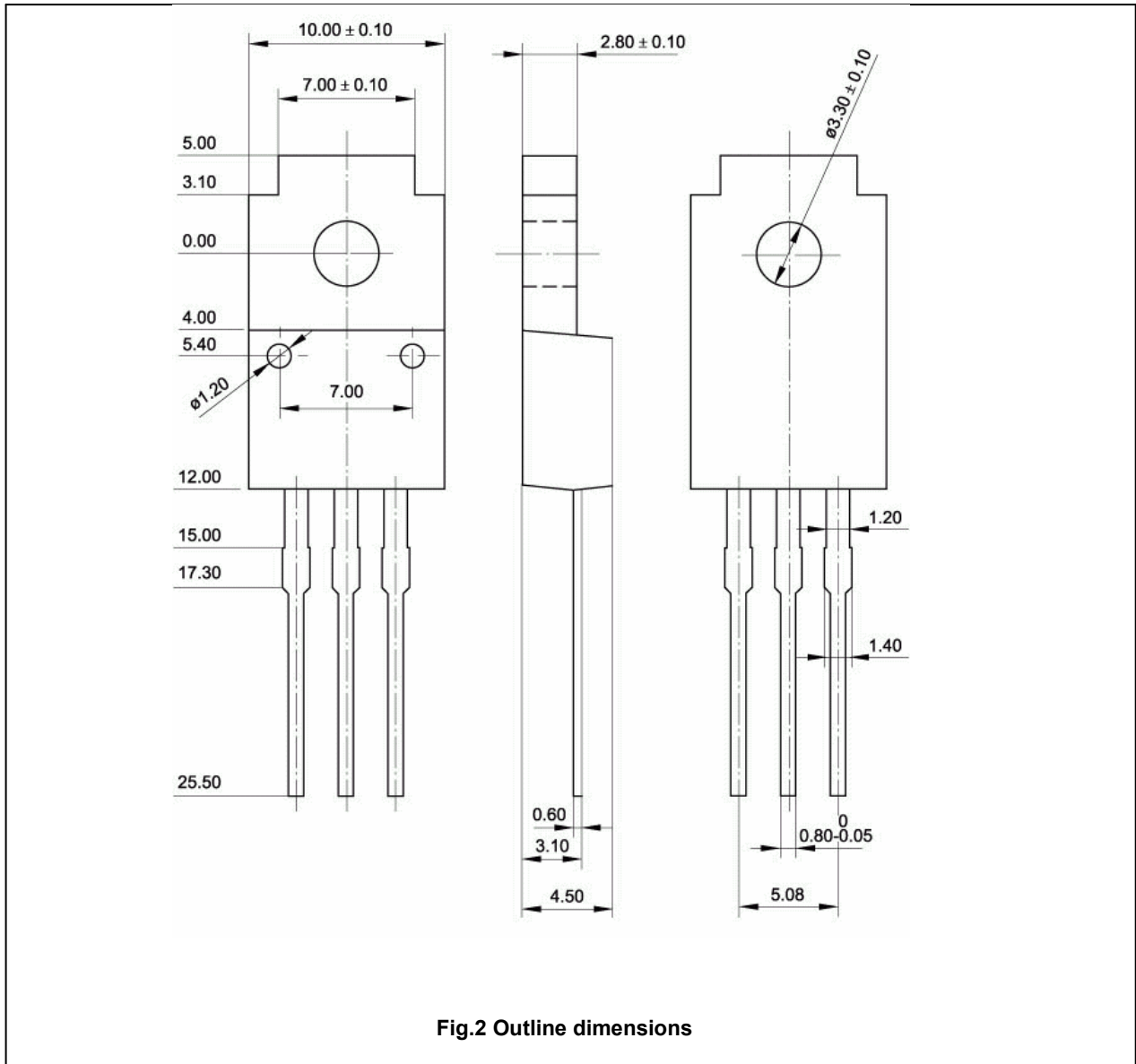


Fig.2 Outline dimensions

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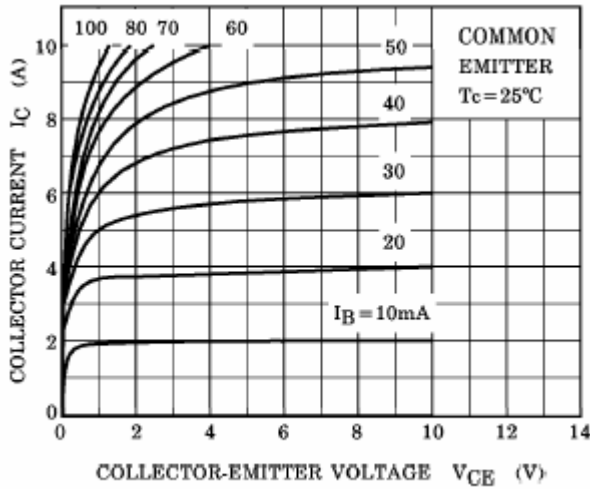


Fig.3 Static Characteristic

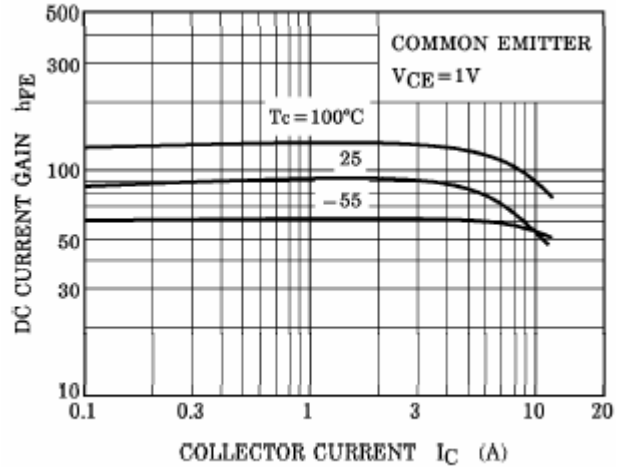


Fig.4 DC current Gain

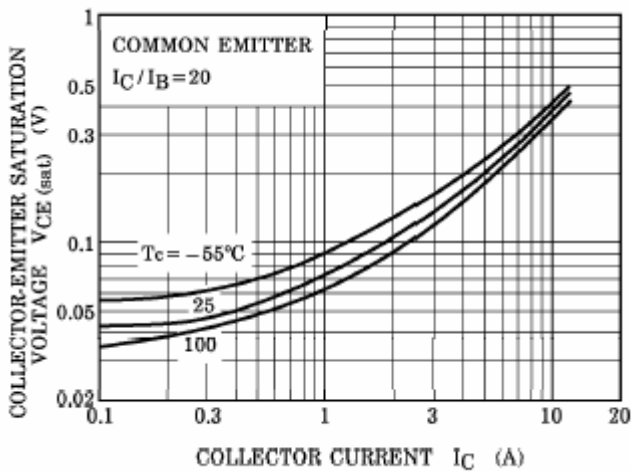


Fig.5 Collector-Emitter Saturation Voltage

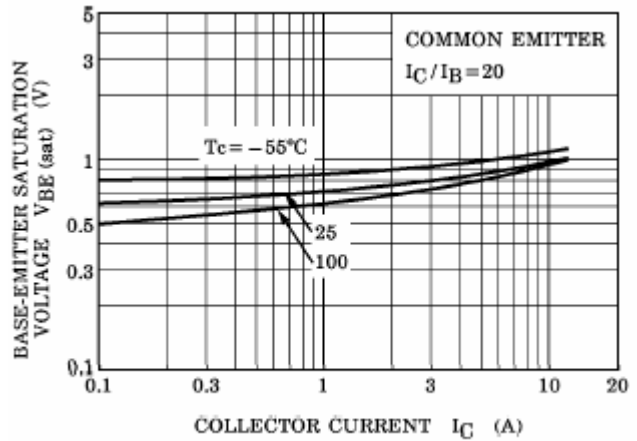


Fig.6 Base-Emitter Saturation Voltage

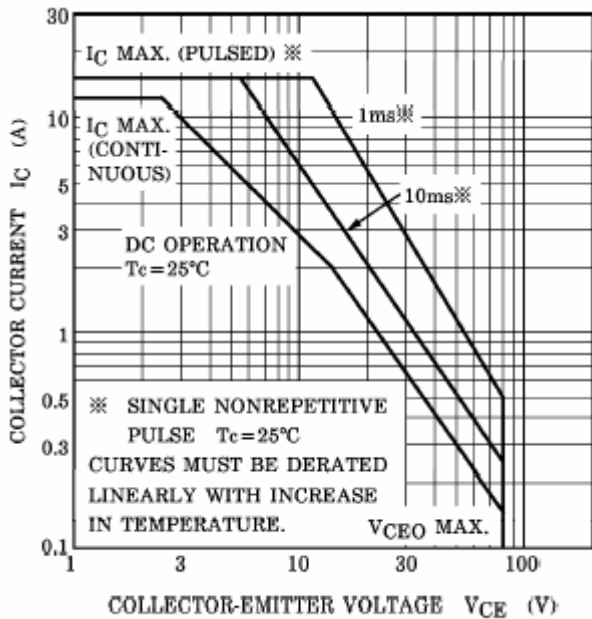


Fig.7 Safe Operating Area